

NCE N-Channel Enhancement Mode Power MOSFET

General Features

• $V_{DS} = 60V, I_D = 0.115A$

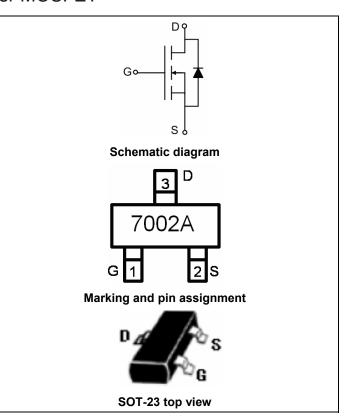
 $R_{DS(ON)}$ < 3.5 Ω @ V_{GS} =5V

 $R_{DS(ON)} < 3\Omega$ @ V_{GS} =10V

- Lead free product is acquired
- Surface mount package

Application

- Direct logic-level interface: TTL/CMOS
- Drivers: relays, solenoids, lamps, hammers, display, memories, transistors, etc.
- Battery operated systems
- Solid-state relays



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
7002A	2N7002A	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (TC=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	60	V	
Gate-Source Voltage	V _{GS}	±20	V	
Drain Current-Continuous@ Current-Pulsed (Note 1)	I _D	0.115	Α	
Drain Current-Continuous@ Current-Pulsed	I _{DM}	0.8	Α	
Maximum Power Dissipation	P _D	0.2	W	
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}\mathbb{C}$	

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	625	°C/W
· ·	1	1	1

Electrical Characteristics (TC=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	68	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA



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Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1	1.7	2.5	V
Drain-Source On-State Resistance	P	V _{GS} =5V, I _D =0.05A	-	2.3	3.5	Ω
Diani-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =0.5A	-	2.1	3	Ω
Forward Transconductance	G FS	V _{DS} =10V,I _D =0.2A	0.08	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V _{DS} =30V,V _{GS} =0V,	-	20	50	PF
Output Capacitance	Coss	F=1.0MHz	-	10	20	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0WHZ	-	3.6	5	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	10	-	nS
Turn-on Rise Time	t _r	V_{DD} =30V, I_{D} =0.2A	-	50	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =10 Ω	-	17	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q_{g}	V _{DS} =10V,I _D =0.115A, V _{GS} =4.5V	-	1.7	3	nC
Drain-Source Diode Characteristics	<u>.</u>		•		•	
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =0.115A	-	-	1.2	٧
Diode Forward Current (Note 2)	Is		-	-	0.115	Α
		•				

Notes:

- $\textbf{1.} \ \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production

Pb Free Product

Typical Electrical and Thermal Characteristics

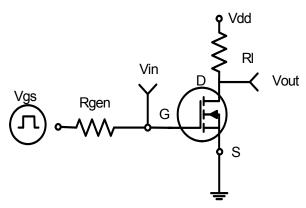


Figure 1:Switching Test Circuit

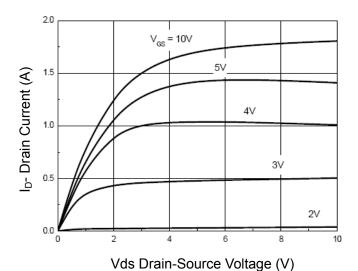


Figure 3 Output Characteristics

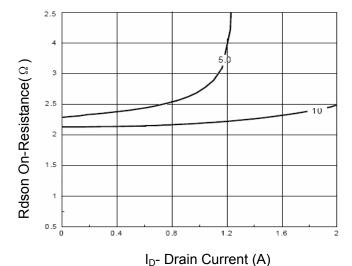


Figure 5 Drain-Source On-Resistance

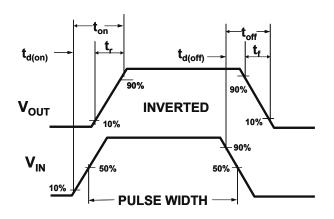


Figure 2:Switching Waveforms

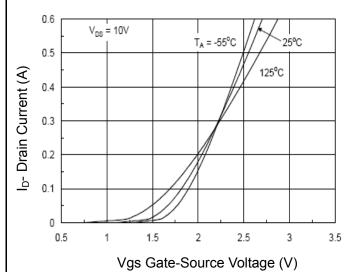
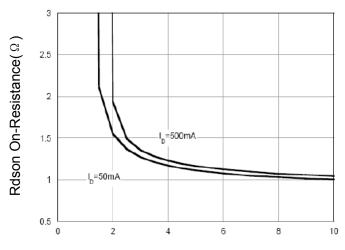


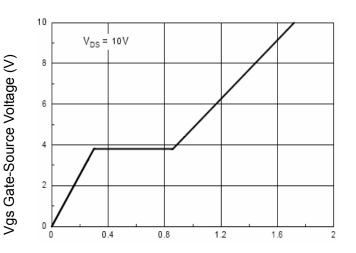
Figure 4 Transfer Characteristics



Vgs Gate-Source Voltage (V)

Figure 6 Rdson vs Vgs





Qg Gate Charge (nC) Figure 7 Gate Charge

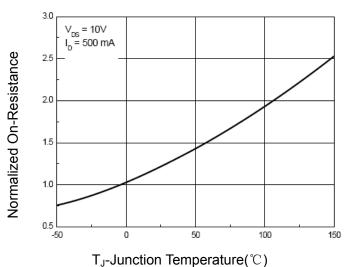


Figure 9 Drain-Source On-Resistance

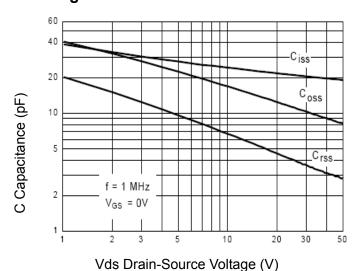
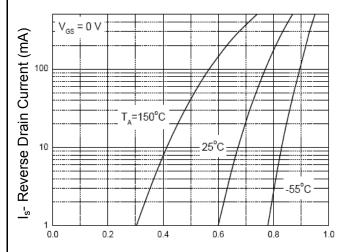
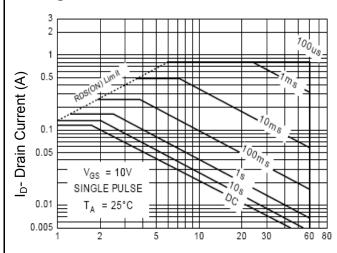


Figure 11 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 8 Source-DrainDiode Forward



Vds Drain-Source Voltage (V)

Figure 10 Safe Operation Area

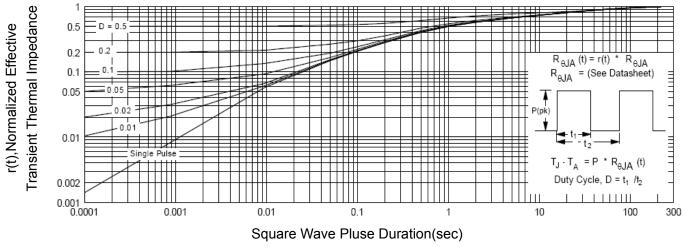
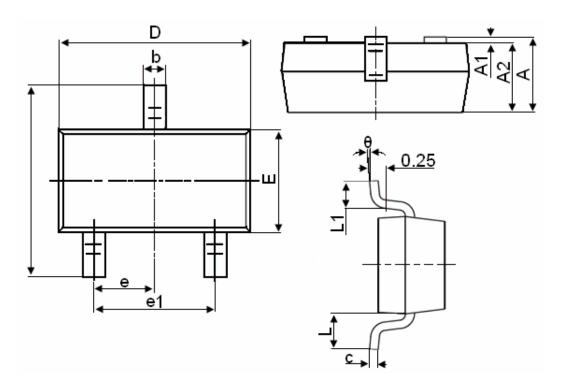


Figure 12 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Information



Symbol	Dimensions in Millimeters				
Symbol	MIN.	MAX.			
Α	0.900	1.150			
A1	0.000	0.100			
A2	0.900	1.050			
b	0.300	0.500			
С	0.080	0.150			
D	2.800	3.000			
E	1.200	1.400			
E1	2.250	2.550			
е		0.950TYP			
e1	1.800	2.000			
L		0.550REF			
L1	0.300	0.500			
θ	0°	8°			

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$

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